

C1 cont substrate 12, controlling the thickness of the LC layer 18, and suppressing disclination, so as to obtain an excellent image quality.

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**IN THE CLAIMS:**

**Please enter the following amended claims:**

C2 10. (Amended) The method of claim 9, further comprising forming a film on said second substrate and patterning said film to form said black matrix.

11. (Amended) The method of claim 10, wherein said step of forming a film comprises forming a chrome film on said second substrate and patterning said chrome film to form said black matrix.

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C3 16. (Amended) The method of claim 9, further comprising positioning a plurality of polarizing plates for sandwiching said first substrate and said second substrate between said polarizing plates.

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C4 18. (Amended) The method of claim 9, wherein forming said gate insulating film comprises silicon oxide, an amorphous silicon layer and a N<sup>+</sup> type amorphous silicon layer formed on said scanning lines and common electrodes.

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